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Abstract

Process for producing metal-containing thin films with a low electrical resistance

The invention relates to a process for producing metal-containing thin films with a low electrical resistance, in which first of all a metal-containing layer (5') with a first grain size is formed up to a recrystallization thickness (d1), and then, at this recrystallization thickness (d1), a recrystallization is carried out in order to produce a metal-containing layer (5'') with a larger grain size. Finally, the metal-containing layer (5'') with the larger grain size is thinned to a desired target thickness (d2), resulting in a very thin metal-containing layer with an electrical resistance which is reduced further.

Figures 3a to 3c



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